

























-  Drafts
-  Pending
-  Active
 -  L1: (16785) multilevel
 -  L2: (18492) multi adj2 level
 -  L3: (1901371) current
 -  L4: (1493450) third
 -  L5: (32439) 1 or 2
 -  L6: (37) 3 with 4 with 5
 -  L7: (201105) nitride
 -  L8: (2) 6 and 7
 -  L9: (501) trapping with 7
 -  L10: (13) 9 same 5
 -  L11: (14) sunkavalli-ravi-s.in.
 -  L12: (201113) 11 7
 -  L13: (6) 11 and 7
 -  L14: (6434) multi adj2 value
 -  L15: (0) 3 with 4 with 14
 -  L16: (64294) 3 with 4
 -  L23: (10) 16 and 14 and 7
-  Failed
-  Saved
-  Favorites
-  Tagged (0)

Search

DBs: USPAT; US-PGPUB; EPO; JPO; DERWENT; IB ☐ Plurals

Default operator: OR ☒ Highlight all hit terms initially

16 and 14 and ?

BR5 f... IS&R... Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	F
1			US 20030043621 A1	20030306	24	Bit line reference circuits for bin 365/185.03			
2			US 20020149061 A1	20021017	42	Nonvolatile memory cell, operating	257/365		
3			US 20020149060 A1	20021017	42	Nonvolatile memory cell, operating	257/365		
4			US 20020131309 A1	20020919	29	Memory, writing apparatus, reading	365/200		
5			US 6424002 B1	20020723	37	Transistor, transistor array and no	257/316	257/317	
6			US 6388293 B1	20020514	36	Nonvolatile memory cell, operating	257/365	257/324;	
7			US 6144585 A	20001107	17	Semiconductor storage device for st	365/185.22	365/185.21	
8			US 5840704 A	19990817	13	Method of manufacturing a reference	438/257	257/E21 68	